

ACJT105-6W 1A TRIAC

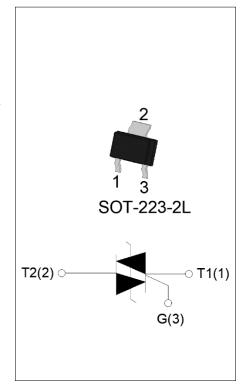
Rev.A.1.0

DESCRIPTION:

The ACJT105-6W triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT105-6W embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package SOT-223-2L is RoHS compliant.

MAIN FEATURES

Symbol	Symbol Value	
I _{T(RMS)}	1	Α
V _{DRM} /V _{RRM}	600	V
I _{GT I} /III/III	5/5/5	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40-150	${\mathbb C}$
Operating junction temperature range	Tj	-40-125	$^{\circ}$
Repetitive peak off-state voltage (T _j =25°C)	VDRM	600	V
Repetitive peak reverse voltage (T _j =25°C)	V_{RRM}	600	V
RMS on-state current (Tc≤90°C)	I _{T(RMS)}	1	Α
Non repetitive surge peak on-state current (full cycle , t_p =20ms , T_j =25 $^{\circ}$ C)	Ттѕм	15	Α
Non repetitive surge peak on-state current (full cycle , t_p =16.6ms , T_j =25 $^{\circ}$ C)	IISM	16.5	A
I^2t value for fusing (tp=10ms , Tj=25 $^{\circ}\!$	l ² t	1.25	A ² s
Critical rate of rise of on-state current (I _G = $2\times$ I _G T , f=100Hz , T _j =125 $^{\circ}$ C)	dl/dt	50	A/µs
Peak gate current (t_p =20 μs , T_j =125 $^{\circ}$ C)	I _{GM}	2	Α
Average gate power dissipation (T _j =125°C)	P _{G(AV)}	0.1	W
Peak gate power	P _{GM}	5	W

TEL: +86-513-68528666 http://www.jjwdz.com



Peak pulse voltage	\/	2.5	ls\ /
(T _j =25 °C; non-repetitive,off-state;FIG.8)	Vpp	3.5	ΚV

ELECTRICAL CHARACTERISTICS (T_j =25 $^{\circ}$ C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
lgт	V _D =12V R _L =33Ω	I - II -III	MAX.	5	mA
V _G т	VD=12V KL=3312	I - II -III	MAX.	1	V
V _{GD}	$V_D = V_{DRM} T_j = 125^{\circ}C$ $R_L = 3.3K\Omega$ $I - II - III$		MIN.	0.2	V
1.	1 4 01	I -III	MAX.	10	m A
IL.	IL IG =1.2IGT	II WAX.	20	mA	
lн	I _T =100mA		MAX.	10	mA
dV/dt	V _D =400V Gate Open T _j =125°C		MIN.	700	V/µs
(dl/dt)c	(dV/dt)c=10V/µs, T _j =125℃		MIN.	0.5	A/ms
ton	I _G =10mA I _A =200mA I _R =20mA		TVD	2	
t _{off}	T _j =25℃		TYP.	20	μs
V _{CL}	I _{CL} =0.1mA t _p =1ms		MIN.	700	V

STATIC CHARACTERISTICS

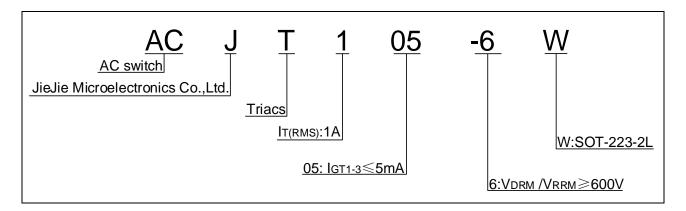
Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	Ітм =1.1A t _p =380µs	T _j =25℃	1.4	V
Vто	Threshold voltage	T _j =125℃	0.8	V
Rd	Dynamic resistance	T _j =125℃	287	mΩ
I _{DRM}	VD=VDRM VR=VRRM	T _j =25℃	5	μΑ
I _{RRM}	VD=VDRM VR=VRRM	T _j =125℃	0.15	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	25	°C/W
R _{th(j-a)}	junction to ambient (AC)	140	°C/W



ORDERING INFORMATION



MARKING

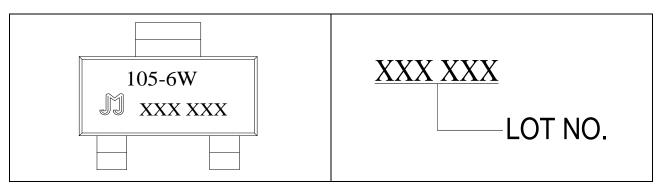


FIG.1 Maximum power dissipation versus RMS on-state current

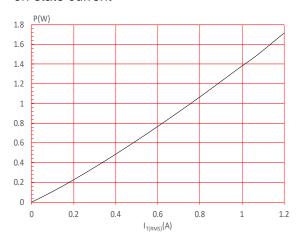


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35µm)(full cycle)

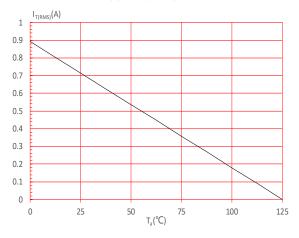


FIG.5: On-state characteristics

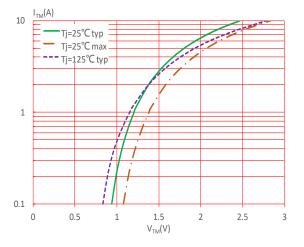


FIG.2: RMS on-state current versus case temperature

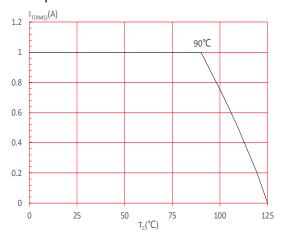


FIG.4: Surge peak on-state current versus number of cycles

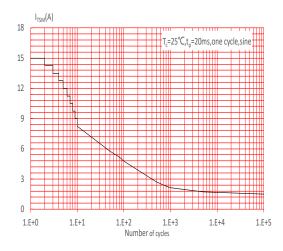


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p <20ms, and corresponding value of I^2t (dI/dt<50A/ μ s)

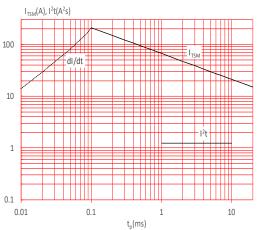


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

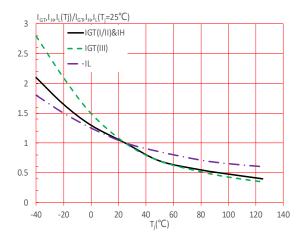
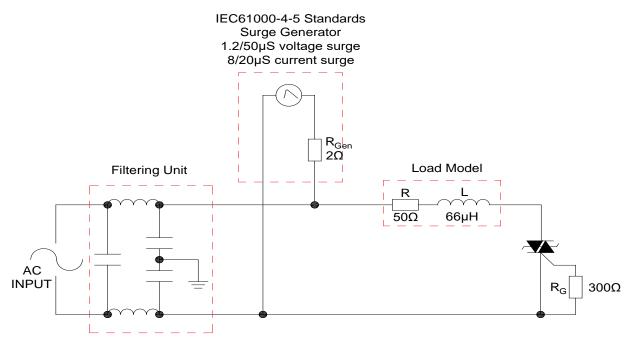
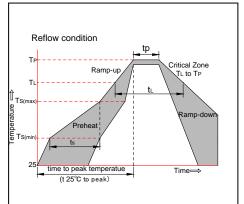


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
	-Temperature Min (T _{s(min)})	+150℃
Pre Heat	-Temperature Max(T _{s(max)})	+200℃
riodi	-Time (Min to Max) (ts)	60-180 secs.
	ramp up rate Temp (T∟)to peak)	3°C/sec. Max
T _{s(max)} to	T _L - Ramp-up Rate	3°C/sec. Max
Defless	-Temperature(T _L)(Liquidus)	+217 ℃
Reflow	-Temperature(t _L)	60-150 secs.
Peak Tem	np (T _p)	+260(+0/-5)°C
Time within 5°C of actual Peak Temp (tp)		20-40secs.
Ramp-do	wn Rate	6°C/sec. Max
Time 25°	to Peak Temp (T _P)	8 min. Max
Do not ex	ceed	+260 ℃





ORDERING INFORMATION

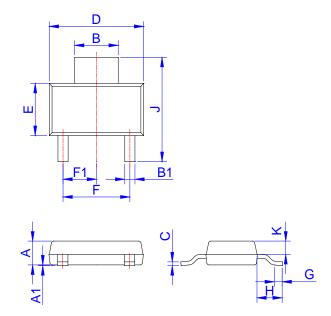
Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT105-6W	600	5	SOT-223-2L	4,000	Tape & Reel

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated

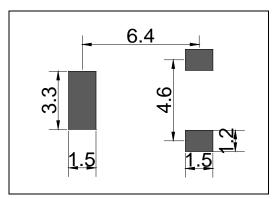


PACKAGE MECHANICAL DATA



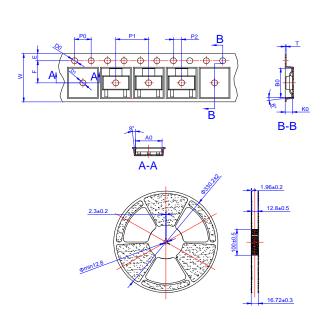
	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	1.50	1.60	1.80	0.059	0.063	0.071	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
В	2.90	3.00	3.10	0.114	0.118	0.122	
B1	0.60	0.70	0.80	0.024	0.028	0.031	
С	0.22	0.254	0.32	0.009	0.010	0.013	
D	6.30	6.50	6.70	0.248	0.256	0.264	
Е	3.30	3.50	3.70	0.130	0.138	0.146	
F	4.40		4.80	0.173		0.189	
F1	2.20		2.40	0.087		0.094	
G	0.50		1.00	0.020		0.039	
Н	1.50	1.75	2.00	0.059	0.069	0.079	
J	6.70	7.00	7.30	0.264	0.276	0.287	
K	0.80		1.00	0.031		0.039	

FOOTPRINT-SOT-223-2L (dimensions in mm)





DELIVERY MODE



	Dimensions						
Ref.	ı	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
W	-	-	12.30	-		0.482	
Е	1.65	1.75	1.85	0.065	0.069	0.073	
F	5.45	5.50	5.55	0.215	0.217	0.219	
D0	1.50	1.55	1.60	0.059	0.061	0.063	
D1	1.50	-	-	0.059	-	-	
P0	3.90	4.00	4.10	0.154	0.157	0.161	
P1	7.90	8.00	8.10	0.311	0.315	0.319	
P2	1.95	2.00	2.05	0.077	0.079	0.081	
10P0	39.80	40.00	40.20	1.567	1.575	1.583	
A0	6.85	6.95	7.05	0.269	0.273	0.276	
В0	7.15	7.25	7.35	0.280	0.284	0.288	
K0	1.95	2.05	2.15	0.076	0.080	0.084	
Т	0.20	0.25	0.30	0.008	0.010	0.012	

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
SOT-223-2L	TAPING	4,000	40,000	13 inch



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd. Copyright ©2023 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.